# 74HC1G32; 74HCT1G32

# 2-input OR gate

Rev. 05 — 14 March 2008

Product data sheet

#### 1. General description

74HC1G32 and 74HCT1G32 are high-speed Si-gate CMOS devices. They provide a 2-input OR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC32 and 74HCT32.

#### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

### 3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74HC1G32GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1					
74HCT1G32GW			body width 1.25 mm						
74HC1G32GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74HCT1G32GV									

#### 4. Marking

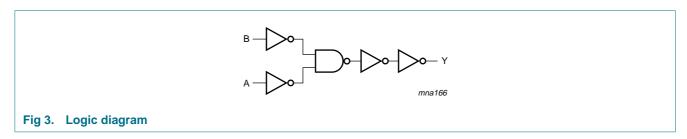
Table 2. Marking codes

Type number	Marking code
74HC1G32GW	HG
74HCT1G32GW	TG
74HC1G32GV	H32
74HCT1G32GV	T32



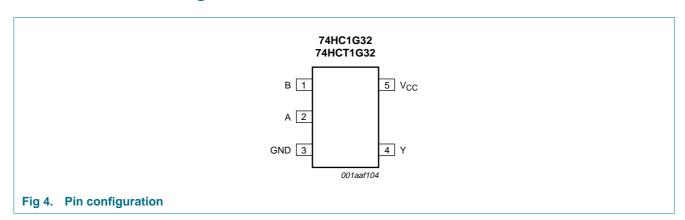
### 5. Functional diagram





### 6. Pinning information

#### 6.1 Pinning



#### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input B
A	2	data input A
GND	3	ground (0 V)
Υ	4	data output Y
$V_{CC}$	5	supply voltage

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### 7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs	Output	
Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
$I_{GND}$	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	200	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	7	4HC1G3	2	74	Unit		
			Min	Тур	Max	Min	Тур	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
$V_{I}$	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$V_{O}$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 \text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

<sup>[2]</sup> Above 55  $^{\circ}\text{C}$  the value of P  $_{tot}$  derates linearly with 2.5 mW/K.

### 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C t	–40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
74HC1G3	2					•			
$V_{IH}$	HIGH-level input	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V	
	voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V	
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V	
$V_{IL}$	LOW-level input	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V	
	voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V	
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V	
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$							
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V	
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V	
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V	
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V	
$V_{OL}$	LOW-level output	$V_I = V_{IH}$ or $V_{IL}$							
	voltage	$I_O = 20 \mu A$ ; $V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	V	
		$I_O = 20 \mu A$ ; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V	
		$I_O = 20 \mu A$ ; $V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V	
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V	
		$I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V	
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ	
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF	
74HCT1G	32								
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V	
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	8.0	V	
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$							
	voltage	$I_O = -20 \mu A$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -2.0 \text{ mA}$	4.13	4.32	-	3.7	-	V	
V <sub>OL</sub>	LOW-level output	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$							
	voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	V	
		I <sub>O</sub> = 2.0 mA	-	0.15	0.33	-	0.4	V	
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ	

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Table 7. Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	Conditions	<b>-40</b> '	°C to +8	35 °C	–40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
$\Delta I_{CC}$	additional supply current	per input; $V_{CC}$ = 4.5 V to 5.5 V; $V_I$ = $V_{CC}$ - 2.1 V; $I_O$ = 0 A	-	-	500	-	850	μΑ
Cı	input capacitance		-	1.5	-	-	-	pF

### 11. Dynamic characteristics

#### Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns. All typical values are measured at  $T_{amb} = 25 \,^{\circ}$ C. For test circuit see Figure 6

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	-40 °C t	Unit	
				Min	Тур	Max	Min	Max	
74HC1G	32	'					'	'	
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	18	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	8	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	8	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	7	20	-	23	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	19	-	-	-	pF
74HCT1	G32								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	10	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	20	-	-	-	pF

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz

f<sub>o</sub> = output frequency in MHz

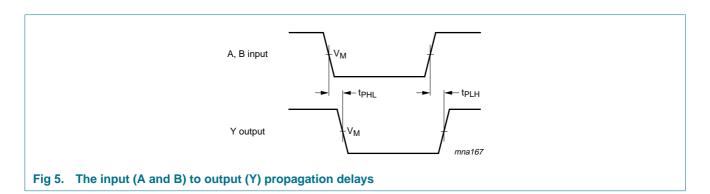
C<sub>L</sub> = output load capacitance in pF

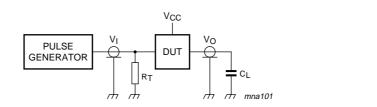
 $V_{CC}$  = supply voltage in V

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$ 

<sup>[2]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu W$ ).

#### 12. Waveforms





Measurement points are given in Table 8. Definitions for test circuit:

 $C_L$  = Load capacitance including jig and probe capacitance.

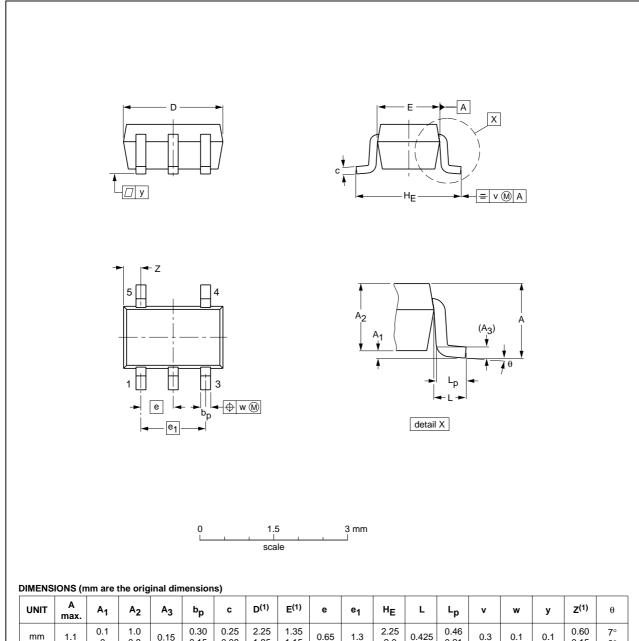
 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

Fig 6. Load circuitry for switching times

### 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	HE	L	Lp	v	w	у	Z <sup>(1)</sup>	θ	
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°	

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

	OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
	VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
	SOT353-1		MO-203	SC-88A		<del>-00-09-01-</del> 03-02-19	
l					,	00 02 10	

Fig 7. Package outline SOT353-1 (TSSOP5)

#### Plastic surface-mounted package; 5 leads

**SOT753** 

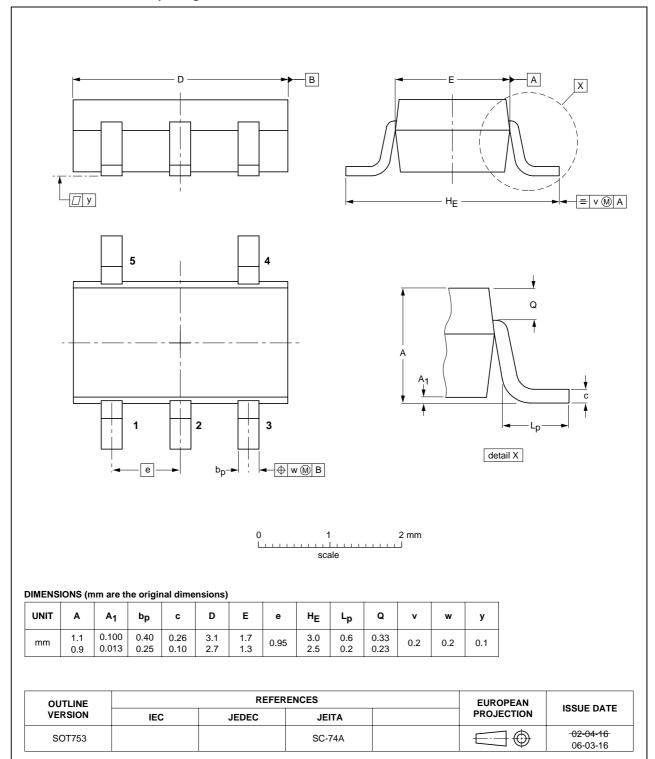


Fig 8. Package outline SOT753 (SC-74A)

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### 14. Abbreviations

#### Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

## 15. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G32_5	20080314	Product data sheet	-	74HC_HCT1G32_4
Modifications:	<ul> <li>Pin descript</li> </ul>	tion of Pin 4 changed from inp	ut to output in <u>Table 3</u>	<u>3</u> .
74HC_HCT1G32_4	20070514	Product data sheet	-	74HC_HCT1G32_3
74HC_HCT1G32_3	20020515	Product specification	-	74HC_HCT1G32_2
74HC_HCT1G32_2	20010406	Product specification	-	74HC_HCT1G32
74HC_HCT1G32	19971216	Preliminary specification	-	-

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#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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